



PTO/SB/08a (08-03)

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 1 Of 1

Complete If Known

Application Number	10/849,347
Filing Date	May 19, 2004
First Named Inventor	Robert H. Burgener, II
Group Art Unit	
Examiner Name	
Attorney Docket Number	3398.2.8

U.S. PATENT DOCUMENTS

Examiner Initials *	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code ² (if known)			
7P	U1	US-2003/0226499	12/11/2003	Teherani	
	U2	US-6,589,362-B2	07/08/2003	Haga	
	U3	US-6,610,141-B2	08/26/2003	White et al.	
	U4	US-6,617,183-B2	09/09/2003	Kadota et al.	
	U5	US-6,624,441-B2	09/23/2003	Cantwell et al.	
	U6	US-6,664,565-B1	12/16/2003	Sano et al.	
7P	U7	US-6,673,478-B2	01/06/2004	Kato et al.	

Examiner Signature	H. Picard	Date Considered	2/17/04
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NON PATENT LITERATURE DOCUMENTS

Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
74	01	Itani, Kenya, et al., "Low-Dislocation-Density GaAs Wafers Grown by Vertical Gradient Freeze Process, Suitable for Mass Production of Semiconductor Lasers," Hitachi Cable Review No. 20, August 2001, pp. 35-38	
	02	Look, D.C., et al. "The Future of ZnO Light Emitters," Phys. Stat. Sol. (2004), pp. 1-10	
	03	Pearson, S.J., et al. "Wide Band Gap Ferromagnetic Semiconductors and Oxides," Journal of Applied Physics Vol. 93, No. 1, January 1, 2003, pp. 1-13	
	04	Web Page '99 SBIR Phase I... Topic 14 – Electronic Materials, http://www-ee.eng.buffalo.edu/faculty/paololin/492/semicon.pdf , "Low-Temperature Hydrothermal Growth of ZnO for Semiconductor Substrates," 2/26/04, 2 pages	
m	05	Web Page "Semiconductor Photonics", 3 pages	

Examiner Signature	74/CMS/AT	Date Considered	2/17/05
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RP	01	Itani, Kenya, et al., "Low-Dislocation-Density GaAs Wafers Grown by Vertical Gradient Freeze Process, Suitable for Mass Production of Semiconductor Lasers," Hitachi Cable Review No. 20, August 2001, pp. 35-38	
	02	Look, D.C., et al. "The Future of ZnO Light Emitters," Phys. Stat. Sol. (2004), pp. 1-10	
	03	Pearson, S.J., et al. "Wide Band Gap Ferromagnetic Semiconductors and Oxides," Journal of Applied Physics Vol. 93, No. 1, January 1, 2003, pp. 1-13	
	04	Web Page '99 SBIR Phase I... Topic 14 – Electronic Materials, http://www-ee.eng.buffalo.edu/faculty/paololin/492/semicon.pdf , "Low-Temperature Hydrothermal Growth of ZnO for Semiconductor Substrates," 2/26/04, 2 pages	
RP	05	Web Page "Semiconductor Photonics", 3 pages	

Examiner Signature	K. Picmont	Date Considered	2/17/05
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